

INFORMATION
DISCLOSURE
CITATION FORM FOR
PATENT APPLICATION
(FORM PTO - 1449)

Docket No.: 306 D12

Serial No.: 10/021,195

Applicant(s): KENNETH COLLINS, ET AL.

Filing Date: 10-30-01

Group: UNKNOWN

RECEIVED
FEB 20 2002
TC 1700

U. S. PATENTS

Initials	Patent No	Issue Date	Name	Class	Subclass	Filing Date
<i>[Signature]</i>	4,123,316	10-31-78	TSUCHIMOTO	X	X	X
<i>[Signature]</i>	4,261,762	04-14-81	KING			
<i>[Signature]</i>	4,350,578	09-21-82	FRIESER ET AL.			
<i>[Signature]</i>	4,368,092	01-11-83	STEINBERG ET AL.			
<i>[Signature]</i>	4,371,412	02-01-83	NISHIZAWA			
<i>[Signature]</i>	4,427,516	01-24-84	LEVINSTEIN ET AL.			
<i>[Signature]</i>	4,427,762	01-24-84	TAKAHASHI ET AL.			
<i>[Signature]</i>	4,430,547	02-07-84	YONEDA ET AL.			
<i>[Signature]</i>	4,457,359	07-03-84	HOLDEN	X	X	X
<i>[Signature]</i>	4,512,391	04-23-85	HARRA			

FOREIGN PATENT DOCUMENTS

Initials	Document Number	Date	Country	Name	Translation? (Yes/No/n/a)
<i>[Signature]</i>	DE 39 42964 A1	27.06.91	GERMANY	ROLAND GESCHE ET AL.	N/A
<i>[Signature]</i>	EP 0 403 418 A2	19.12.90	EUROPE	GREGOR CAMPBELL ET AL.	N/A
<i>[Signature]</i>	EP 0 413 282 A2	20.02.91	EUROPE	JOHN OGLE	N/A
<i>[Signature]</i>	EP 0 520 519 A1	30.12.92	EUROPE	JEFFREY MARKS ET AL.	N/A
<i>[Signature]</i>	EP 0 552 490 A1	28.07.93	EUROPE	JEFFREY MARKS ET AL.	N/A
<i>[Signature]</i>	EP 0 552 491 A1	28.07.93	EUROPE	KENNETH COLLINS ET AL.	N/A

Initials	Other Documents (Title, Author, Date, Pages, Etc., if known)
<i>[Signature]</i>	Coburn, W.J., "Increasing the Etch Rate Ratio oSiO_2/Si in Fluorocarbon Plasma Etching," <i>IBM Technical Disclosure</i> , Vol. 19, No. 10, March 1997.
<i>[Signature]</i>	Cook, J.M., Ibbatson, D.E., and Flamm, D.L., "Application of a low-pressure radio frequency discharge source to polysilicon gate etching," <i>J. Vac. Sci. Technol.</i> , Vol. B8, No. 1, Jan/Feb 1990, pp. 1-5.

Examiner's Signature: <i>[Signature]</i>	Date Considered: 1/21/03
--	--------------------------

Initial if reference was considered, whether or not citation with MPEP. Mark through citation if not considered. Include a copy of this citation form with your next correspondence to the Applicant(s).

INFORMATION
DISCLOSURE
CITATION FORM FOR
PATENT APPLICATION
(FORM PTO - 1449)

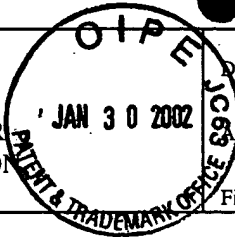
Docket No.: 306 D12

Serial No.: 10/021,195

Applicant(s): KENNETH COLLINS, ET AL.

Filing Date: 10-30-01

Group: UNKNOWN



U. S. PATENTS

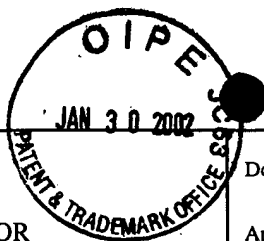
Initials	Patent No	Issue Date	Name	Class	Subclass	Filing Date
AKM	4,565,601	01-21-86	KAKEHI ET AL.			
	4,572,759	02-29-86	BENZING			
	4,579,080	04-01-86	MARTIN ET AL.			
	4,711,698	12-08-87	DOUGLAS			
	4,755,345	07-05-88	BAITY, JR. ET AL.			
	4,756,810	07-12-88	LAMONT, JR. ET AL.			
	4,786,352	11-22-88	BENZING			
	4,786,359	11-22-88	STARK ET AL.			
	4,793,897	12-27-88	DUNFIELD ET AL.			
	4,793,945	12-27-88	SIREN			

FOREIGN PATENT DOCUMENTS

Initials	Document Number	Date	Country	Name	Translation? (Yes/No/n/a)
AKM	EP 0 596 551 A1	11.05.94	EUROPE	JEFFREY BENZING ET AL.	N/A
	EP 0 601 468 A1	15.06.94	EUROPE	KENNETH COLLINS ET AL.	N/A
	EP 0 641 013 A2	01.03.95	EUROPE	KEVIN FAIRBAIRN ET AL.	N/A
	EP 0 651 434 A2	03.05.95	EUROPE	NICOLAS BRIGHT ET AL.	N/A
	EP 0 680 072 A2	02.11.95	EUROPE	FRED REDECKER ET AL.	N/A
	EP 0 702 391 A2	20.03.95	EUROPE	DIANA MA ET AL.	N/A

Initials	Other Documents (Title, Author, Date, Pages, Etc., if known)
AKM	Horiike, Y., Kubota, K., Shindo, H., and Fukasawa, T., "High rate and highly selective SiO ₂ etching employing inductively coupled plasma and discussion on reaction kinetics," <i>J. Vac. Sci. Technol.</i> , Vol. 13, No.3, May/June 1995, pp.801-809
AKM	Lee, H., Dong-II, Y., and Whang, J., "The effects of magnetic fields on a planar inductively coupled argon plasma," <i>Plasma Sources Sci. Technol.</i> , 5(1996), pp. 383-388.

Examiner's Signature: <i>R. Anderson</i>	Date Considered: <i>01/21/03</i>
Initial if reference was considered, whether or not citation with MPEP. Mark through citation if not considered. Include a copy of this citation form with your next correspondence to the Applicant(s).	

INFORMATION
DISCLOSURE
CITATION FORM FOR
PATENT APPLICATION
(FORM PTO - 1449)

Docket No.: 306 D12

Serial No.: 10/021,195

Applicant(s): KENNETH COLLINS, ET AL.

Filing Date: 10-30-01

Group: UNKNOWN

RECEIVED
FEB 20 2002
TC 1700

U. S. PATENTS

Initials	Patent No	Issue Date	Name	Class	Subclass	Filing Date
DKM	4,795,529	01-03-89	KAWASAKI ET AL.			
	4,807,016	02-21-89	DOUGLAS			
	4,810,935	03-07-89	BOSWELL			
	4,828,369	05-09-89	HOTOMI			
	4,842,683	06-27-89	CHENG ET AL.			
	4,844,775	07-04-89	KEEBLE			
	4,849,675	07-18-89	MULLER			
	4,859,908	08-22-89	YOSHIDA ET AL.			
	4,870,245	09-26-89	PRICE ET AL.			
	4,918,031	04-17-90	FLAMM ET AL.			
✓	4,948,458	08-14-90	OGLE			

FOREIGN PATENT DOCUMENTS

Initials	Document Number	Date	Country	Name	Translation? (Yes/No/n/a)
DKM	EP 0 710 055 A1	01.05.96	EUROPE	XUE-YU QIAN ET AL.	N/A
	EP 0 727 807 A1	21.08.96	EUROPE	HIROJI HANAWA	N/A
	EP 0 727 923 A1	12.08.96	EUROPE	HIROJI HANAWA	N/A
	EP 0 742 577 A2	31.11.96	EUROPE	YAN YE ET AL.	N/A
	EP 0 756 309 A1	29.01.97	EUROPE	KENNETH COLLINS ET AL.	N/A
	EP 0 807 952 A2	19.11.97	EUROPE	KENNETH COLLINS ET AL.	N/A
	EP 0 837 489 A2	22.04.98	EUROPE	KENNETH COLLINS, ET AL.	N/A
✓	EP 0 892 422 A2	20.01.99	EUROPE	KENNETH COLLINS ET AL.	N/A

Initials	Other Documents (Title, Author, Date, Pages, Etc., if known)
DKM	Lieberman, M.A., and Ashida, S., "Global models of pulse-power-modulated high-density, low pressure discharges," <i>Plasma Sources Sci. Technol.</i> , 5(1996), pp. 145-158.
✓	Matsuo, Seitaro, "Selective Etching of siO ₂ Relative to Si by Plasma Reactive Sputter Etching," <i>J. Vac. Sc. Technology</i> , Vol. 17, No. 2, March-April 1980.

Examiner's Signature:

Date Considered:

01/21/03

INFORMATION
DISCLOSURE
CITATION FORM FOR
PATENT APPLICATION
(FORM PTO - 1449)

Docket No.: 306 D12

Serial No.: 10/021,195

Applicant(s): KENNETH COLLINS, ET AL.

Filing Date: 10-30-01

Group: UNKNOWN

RECEIVED
FEB 26 2002
TC 1700

U. S. PATENTS

Initials	Patent No	Issue Date	Name	Class	Subclass	Filing Date
RCM	4,948,750	08-14-90	KAUSCHE ET AL.	X		
	4,990,229	02-05-91	CAMPBELL ET AL.			
	5,000,113	03-19-91	WANG ET AL.			
	5,006,220	04-09-91	HIJIKATA ET AL.			
	5,015,330	05-14-91	OKUMURA ET AL.			
	5,032,202	06-16-91	TSAI ET AL.			
	5,074,456	12-24-91	DEGNER ET AL.			
	5,085,727	02-04-92	STEGE			
	5,122,251	06-16-92	CAMPBELL ET AL.			
	5,169,487	12-08-92	LANGLEY ET AL.			
	5,173,412	12-22-92	KIENER ET AL.			

FOREIGN PATENT DOCUMENTS

Initials	Document Number	Date	Country	Name	Translation? (Yes/No/n/a)
RCM	GB 231,197	07.11.90	GREAT BRITAIN	MERVYN DAVIS ET AL.	N/A
	JP 55-9464	23.01.80	JAPAN	OSAMU OZAWA	YES
	JP 55-154582	02.12.80	JAPAN	TOYOTA HIROYASU ET AL.	N/A
	JP 57-155732	25.09.82	JAPAN	RIYOUHEI KAWABATA	YES
	JP 61-147531	21.12.84	JAPAN	OTANI YASIKAZU	N/A
	JP 61-91377	09.05.86	JAPAN	ATSUSHI SEKIGUCHI ET AL.	N/A

Initials	Other Documents (Title, Author, Date, Pages, Etc., if known)
RCM	Oerhlein, G., and Lee, Y., "Reactive ion etching related Si surface residues and subsurface damage: Their relationship to fundamental etching mechanisms," <i>J. Vac. Sci. Technol.</i> , Vol. 5, No. 4, Jul/Aug 1987, pp. 1585-1594.
RCM	Perry, A.J., Vender, D., and Boswell, R.W., "The application of the helicon source to plasma processing," <i>J. Vac. Sci. Technol.</i> , Vol. 9, No. 2, March/April 1991, pp. 310-317.
RCM	Samukawa, S., and Ohtake, H., "Pulse-time Modulated Plasma Etching for Precise ULSI Patterning," Abstract No. 162, <i>Microelectronics Research Laboratories</i> , NEC Corporation, Japan, May 1996, pp. 217-218.

Examiner's Signature:

Date Considered:

01/21/03



RECEIVED
FEB 28 2002
Page No. 5 of 8
TC 1700

INFORMATION
DISCLOSURE
CITATION FORM FOR
PATENT APPLICATION
(FORM PTO - 1449)

Docket No.: 306 D12 Serial No.: 10/021,195
Applicant(s): KENNETH COLLINS, ET AL.
Filing Date: 10-30-01 Group: UNKNOWN

U. S. PATENTS

Initials	Patent No	Issue Date	Name	Class	Subclass	Filing Date
RCM	5,187,454	02-16-93	COLLINS ET AL.			
	5,203,956	04-20-93	HANSEN			
	5,210,466	05-11-93	COLLINS ET AL.			
	5,226,154	07-06-93	KONDOH			
	5,241,245	08-31-93	BARNES ET AL.			
	5,249,251	09-28-93	EGALON ET AL.			
	5,258,824	11-02-93	CARLSON ET AL.			
	5,271,788	12-21-93	HASEGAWA ET AL.			
	5,275,683	01-04-94	ARAMI ET AL.			
	5,276,693	01-04-94	LONG ET AL.			
	5,277,751	01-11-94	OGLE			
	5,326,404	07-05-94	SATO			

FOREIGN PATENT DOCUMENTS

Initials	Document Number	Date	Country	Name	Translation? (Yes/No/n/a)
RCM	JP 61-142744	30.06.86	JAPAN	SHINGO KADOMURA	YES
	JP 62-7268	14.01.87	JAPAN	SETSUHIKO UEDA	YES
	JP 62-12129	21.01.87	JAPAN	MASAYOSHI SERIZAWA ET AL.	YES
	JP 62-249422	30.10.87	JAPAN	KOICHIRO KAWAMURA ET AL.	YES
	JP 62-254428	06.11.87	JAPAN	AZIRA OZAWA ET AL.	YES
	JP 63-9120	14.01.88	JAPAN	YOSHISANE OKAMURA	N/A

Initials	Other Documents (Title, Author, Date, Pages, Etc., if known)
RCM	Shibano, T., Fujiwara, N., Hirayama, M., Nagata, H., and Demizu, K., "Etching of SiO ₂ by low energy CF+x and F ⁺ ions," <i>Appl. Phys. Lett.</i> , Vol. 63, No. 17, October 25, 1993, pp. 2336-2338.
RCM	Suagi, H., and Nakamura, K., "Diagnostics and control of radicals in an inductively coupled etching reactor," <i>J. Vac. Sci. Technol.</i> , Vol. 13, No. 3, May/June 1995, pp. 8878-893.

Examiner's Signature: *Richard*

Date Considered: 01/21/03

Initial if reference was considered, whether or not citation with MPEP. Mark through citation if not considered. Include a copy of this citation form with your next correspondence to the Applicant(s).



Page No. 16 of 18

RECEIVED
FEB 26 2002
TC 1700INFORMATION
DISCLOSURE
CITATION FORM FOR
PATENT APPLICATION
(FORM PTO - 1449)

Docket No.: 306 D12

Serial No.: 10/021,195

Applicant(s): KENNETH COLLINS, ET AL.

Filing Date: 10-30-01

Group: UNKNOWN

U. S. PATENTS

Initials	Patent No	Issue Date	Name	Class	Subclass	Filing Date
DLW	5,346,578	09-13-94	BENZING ET AL.			
	5,349,313	09-20-94	COLLINS ET AL.			
	5,392,018	02-21-95	COLLINS ET AL.			
	5,399,237	03-21-95	KESWICK ET AL.			
	5,401,350	03-28-96	PATRICK ET AL.			
	5,414,246	05-09-95	SHAPONA			
	5,421,891	06-06-95	CAMPBELL ET AL.			
	5,423,945	06-13-95	MARKS ET AL.			
	5,449,432	09-12-95	HANAWA			
	5,468,341	11-21-95	SAMUKAWA			

FOREIGN PATENT DOCUMENTS

Initials	Document Number	Date	Country	Name	Translation? (Yes/No/n/a)
DLW	JP 63-155728	28.06.88	JAPAN	YASUhide SATO	YES
	JP 64-15928	19.01.89	JAPAN	YOSHITSUGI FUKUYAMA ET AL.	YES
	JP 4-94121	26.03.92	JAPAN	KAZUhide ONO	YES
	WO 91/10341	11.07.91	PCT	STEPHEN SAVAS ET AL.	N/A
	WO 92/20833	26.11.92	PCT	MARK WEISE ET AL.	N/A
	WO 97/08734	06.03.97	PCT	KENNETH COLLINS ET AL.	N/A

Initials

Other Documents (Title, Author, Date, Pages, Etc., if known)

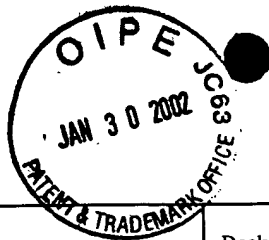
Tynan, GR., Bailey III, A.D., Campbell, G.A., Charatan, R., de Chambrier, A., Gibson, G., Hemker, D.J., Jones, K., Kuthi, A., Lee, C., and Wilcoxson, M., "Characterization of an Azimuthally Symmetric Helicon Wave High Density Plasma Source," *Trikon Technologies, Inc.*, Japan, July 1997.

European Patent Office Communication Pursuant to Article 96(2) and Rule 51(2) EPC for Application No. 94307307.2-2208, mailed January, 1996.

Examiner's Signature: *Alejandro*

Date Considered: 01/21/03

Initial if reference was considered, whether or not citation with MPEP. Mark through citation if not considered. Include a copy of this citation form with your next correspondence to the Applicant(s).



RECEIVED
FEB 12 2002
Page No. 12 Of 12
TC 1700

INFORMATION
DISCLOSURE
CITATION FORM FOR
PATENT APPLICATION
(FORM PTO - 1449)

Docket No.: 306 D12

Serial No.: 10/021,195

Applicant(s): KENNETH COLLINS, ET AL.

Filing Date: 10-30-01

Group: UNKNOWN

U. S. PATENTS

Initials	Patent No	Issue Date	Name	Class	Subclass	Filing Date
RCM	5,477,975	12-26-95	RICE ET AL.			
	5,414,246	05-07-96	BLALOCK			
	5,518,547	05-21-96	BARNES ET AL.			
	5,529,657	06-25-96	ISHII			
	5,556,501	09-17-96	COLLINS ET AL.			
	5,607,542	03-04-97	WU ET AL.			
	5,683,538	11-04-97	O'NEILL ET AL.			
	5,928,528	11-27-99	KUBOTA ET AL.			
	5,935,373	08-10-99	KOSHIMIZU			
	6,024,826	02-15-00	COLLINS ET AL.			
	6,027,606	02-22-00	MOHN ET AL.			
	6,074,512	06-13-00	COLLINS ET AL.			

FOREIGN PATENT DOCUMENTS

Initials	Document Number	Date	Country	Name	Translation? (Yes/No/n/a)

Initials	Other Documents (Title, Author, Date, Pages, Etc., if known)
RCM	PATENT ABSTRACTS OF JAPAN, Publication No. 410079372 A, March 24, 1998 (MATSUSHITA ELECTRIC IND CO LTD)
	PATENT ABSTRACTS OF JAPAN, Publication No. 11026433, January 29, 1999 (MATSUSHITA ELECTRON CORP)
	PATENT ABSTRACTS OF JAPAN, Publication No. 57045927 A, March 16, 1982 (FUJITSU LTD)
	PATENT ABSTRACTS OF JAPAN, Publication No. 62052714 A, March 7, 1987 (OLYMPUS OPTICAL CO. LTD; TOAGOSEI CHEM IND CO LTD)
	PATENT ABSTRACTS OF JAPAN, Publication No. 06196446 A, July 15, 1994 (NEC CORP)
	PATENT ABSTRACTS OF JAPAN, Publication No. 07288196 A, October 31, 1995 (TOKYO ELECTRON LTD)
	PATENT ABSTRACTS OF JAPAN, Publication No. 08017799 A, January 19, 1996 (PLASMA SYST: KK)

Examiner's Signature: *Delegando*

Date Considered: 01/21/03

Initial if reference was considered, whether or not citation with MPEP. Mark through citation if not considered. Include a copy of this citation form with your next correspondence to the Applicant(s).



INFORMATION
DISCLOSURE
CITATION FORM FOR
PATENT APPLICATION
(FORM PTO - 1449)

Docket No.: 306 D12

Serial No.: 10/021,195

Applicant(s): KENNETH COLLINS, ET AL.

Filing Date: 10-30-01

Group: UNKNOWN

RECEIVED
FEB 20 2002
TC 1700

U. S. PATENTS

Initials	Patent No	Issue Date	Name	Class	Subclass	Filing Date
<i>[Signature]</i>	6,054,013	04-25-00	COLLINS ET AL.			
	6,063,233	05-16-00	COLLINS ET AL.			
	6,074,512	06-13-00	COLLINS ET AL.			
	6,077,384	06-20-00	COLLINS ET AL.			
	6,090,303	07-18-00	COLLINS ET AL.			
	6,095,083	08-01-00	RICE ET AL.			
	6,095,084	08-01-00	SHAMOULIAN			
	6,165,311	12-26-00	COLLINS ET AL.			
	6,193,836	02-27-01	MOHN ET AL.			
	6,217,785	04-17-01	COLLINS ET AL.			

FOREIGN PATENT DOCUMENTS

Initials	Document Number	Date	Country	Name	Translation? (Yes/No/n/a)

Initials	Other Documents (Title, Author, Date, Pages, Etc., if known)

Examiner's Signature:

[Signature]

Date Considered:

01/21/03

Initial if reference was considered, whether or not citation with MPEP. Mark through citation if not considered. Include a copy of this citation form with your next correspondence to the Applicant(s).